Amendments to the Claims:

- I. (Currently amended) A structure, comprising:
 - an external terminal:
 - a reference terminal;
- a first transistor formed on a substrate, the first transistor having a current path <u>electrically</u> <u>connected</u> <u>eoupled</u> between the external terminal and the reference terminal;
- a second transistor having a current path <u>electrically connected</u> eoupled between the external terminal and the substrate; and
- a third transistor having a current path <u>electrically connected</u> ecupled between the substrate and the reference terminal, wherein the current paths of the second and third transistors are in parallel with the current path of the first transistor.
- 2. (Original) A structure as in claim 1, further comprising:
- a first resistor coupled between the external terminal and the current path of the second transistor; and
- a second resistor coupled between the current path of the third transistor and the reference terminal.
- 3. (Original) A structure as in claim 1, wherein the substrate is a first lightly doped region having a first conductivity type.
- 4. (Original) A structure as in claim 3, further comprising:
- a first heavily doped region having a second conductivity type and underlying the substrate and the first transistor; and
- a second lightly doped region having the second conductivity type, the second lightly doped region formed at a face of the substrate and extending to the first heavily doped region.
- (Original) A structure as in claim 4, further comprising:
 a first diode coupled between the external terminal and the second lightly doped region; and

a second diode coupled between the reference terminal and the second lightly doped region.

- 6. (Currently amended) A structure as in claim 1, wherein the first transistor further comprises a control terminal electrically connected ecupled to the substrate.
- 7. (Original) A structure as in claim 6, further comprising:
- a first resistor coupled between the external terminal and the current path of the second transistor, and
- a second resistor coupled between the current path of the third transistor and the reference terminal.
- 8. (Original) A structure as in claim 7, wherein the substrate is a first lightly doped region having a first conductivity type, the structure further comprising:
- a first heavily doped region having a second conductivity type and underlying the substrate and the first transistor; and
- a second lightly doped region having the second conductivity type, the second lightly doped region formed at a face of the substrate and extending to the first heavily doped region.
- 9. (Original) A structure as in claim 8, further comprising:
- a first diode having a first terminal coupled to the second lightly doped region and having a second terminal coupled between the first resistor and the current path of the second transistor; and
- a second diode having a first terminal coupled to the second lightly doped region and having a second terminal coupled between the second resistor and the current path of the third transistor.
- 10. (Original) A structure as in claim 9, further comprising: an isolation circuit connected to the external terminal; and a protected circuit electrically connected to the isolation circuit.
- 11. (Original) A structure as in claim 1, further comprising a protected circuit electrically connected to the external terminal.

- 12. (Currently amended) A structure as in claim 1, wherein the first transistor is an MOS transistor having a control gate electrically connected eoupled to the substrate.
- 13. (Currently amended) A structure as in claim 1, wherein the first transistor is a bipolar transistor having a base terminal <u>electrically connected</u> eoupled to the substrate.

Claims 14-45 (cancelled)